

N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV _{DSS}	30V
R _{DS(on)} (MAX.)	35mΩ
I _D	5A



Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _A = 25 °C	I _D	5	A
	T _A = 70 °C		3.3	
Pulsed Drain Current ¹		I _{DM}	20	
Power Dissipation	T _A = 25 °C	P _D	1.04	W
	T _A = 70 °C		0.66	
Operating Junction & Storage Temperature Range		T _j , T _{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Ambient ³	R _{θJA} (T ≤ 10sec)		83	°C / W
	R _{θJA} (Steady State)		120	

¹Pulse width limited by maximum junction temperature.

²Duty cycle ≤ 1%

³The device mounted on a 1 in² pad of 2 oz copper.

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, Unless Otherwise Noted)

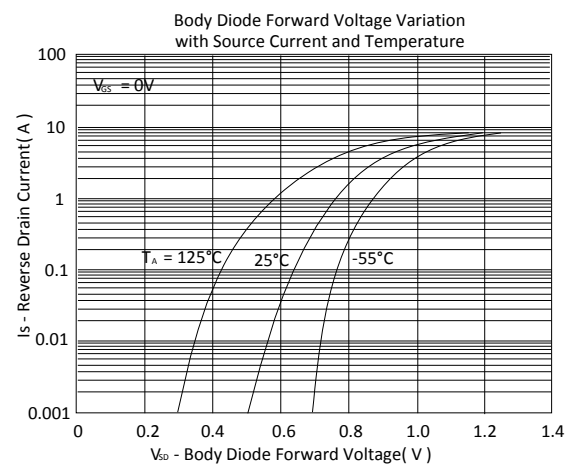
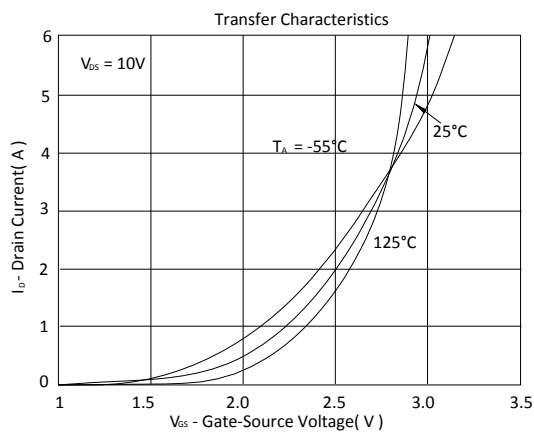
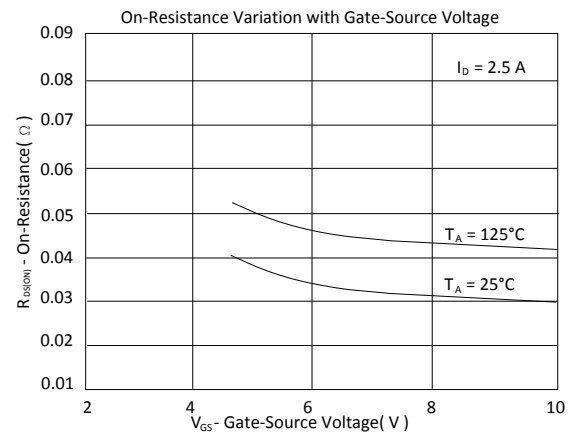
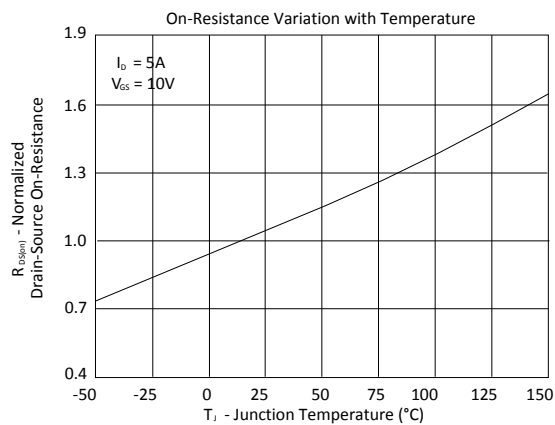
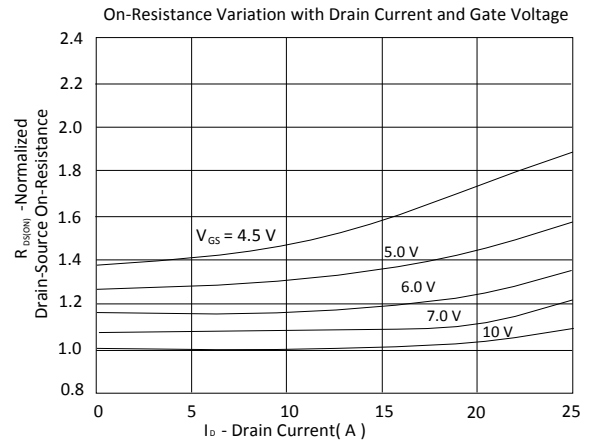
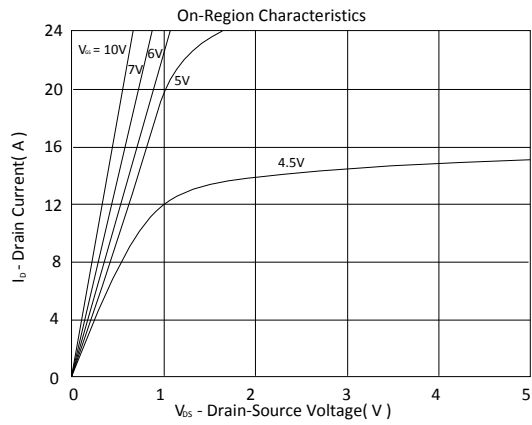
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT	
			MIN	TYP	MAX		
STATIC							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.5	3.0		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$			1	μA	
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			10		
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 5V, V_{GS} = 10V$	5			A	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 5A$		30	35	m Ω	
		$V_{GS} = 4.5V, I_D = 4A$		40	50		
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 5A$		11		S	
DYNAMIC							
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 10V, f = 1MHz$		323		pF	
Output Capacitance	C_{oss}			75			
Reverse Transfer Capacitance	C_{rss}			53			
Total Gate Charge ^{1,2}	Q_g	$V_{DS} = 10V, V_{GS} = 10V, I_D = 5A$		7.1		nC	
Gate-Source Charge ^{1,2}	Q_{gs}			1.1			
Gate-Drain Charge ^{1,2}	Q_{gd}			2.2			
Turn-On Delay Time ^{1,2}	$t_{d(on)}$	$V_{DS} = 15V, I_D = 1A, V_{GS} = 10V, R_{GS} = 6\Omega$		8		nS	
Rise Time ^{1,2}	t_r			12			
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$			28			
Fall Time ^{1,2}	t_f			15			
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_C = 25\text{ }^{\circ}C$)							
Continuous Current	I_S				2	A	
Pulsed Current ³	I_{SM}				8		
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			1.2	V	

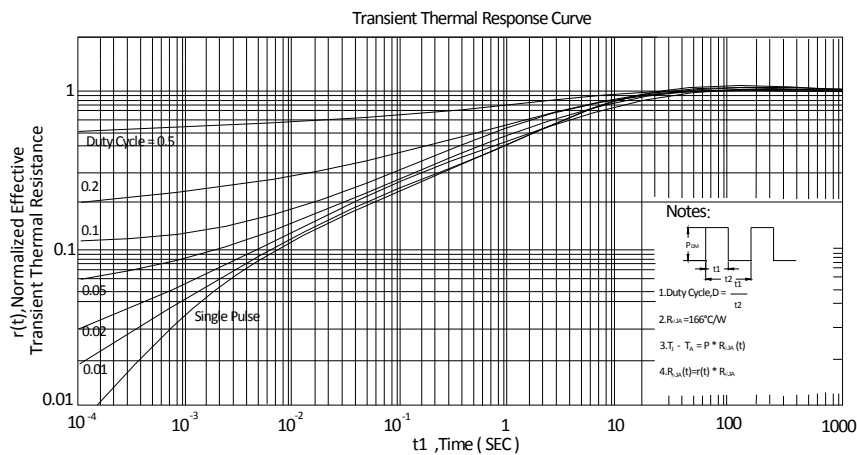
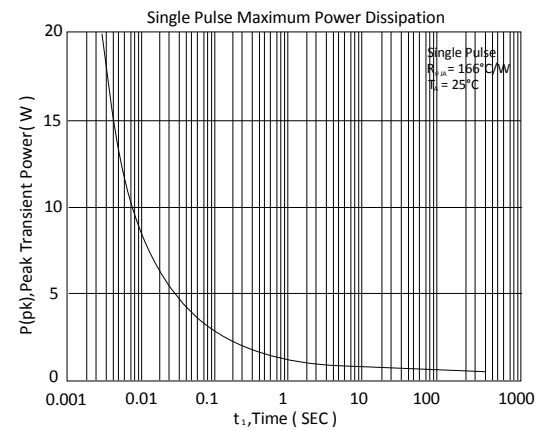
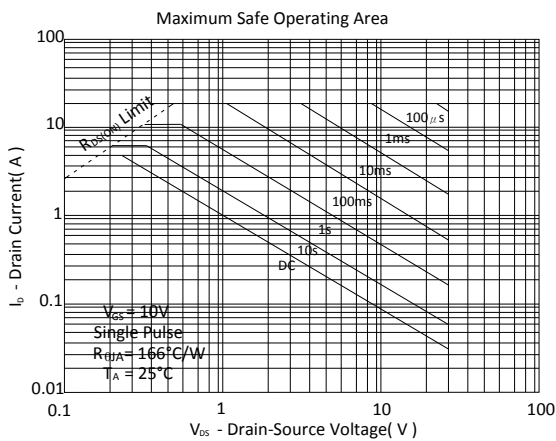
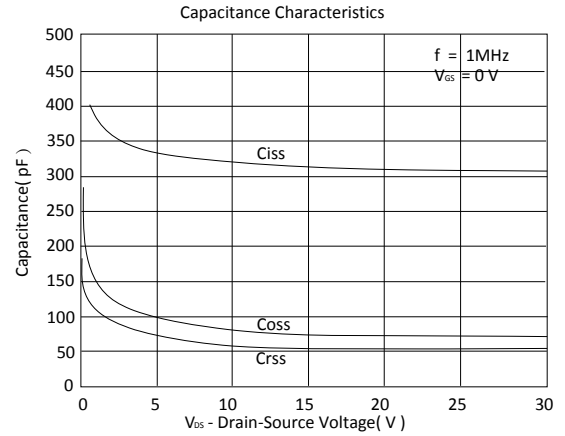
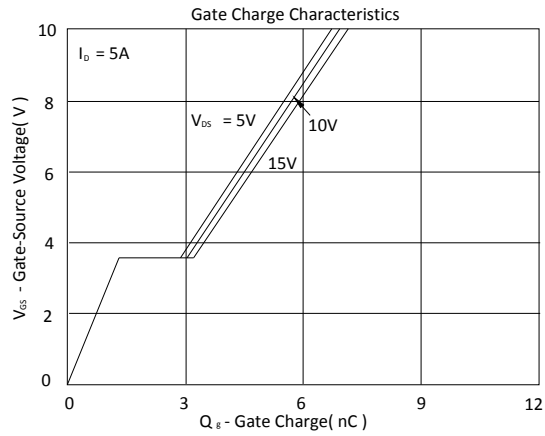
¹Pulse test : Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

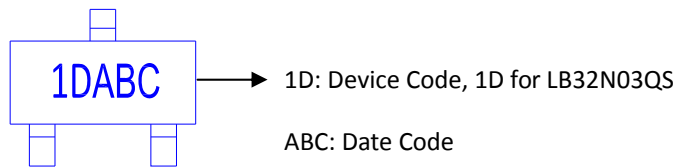
TYPICAL CHARACTERISTICS



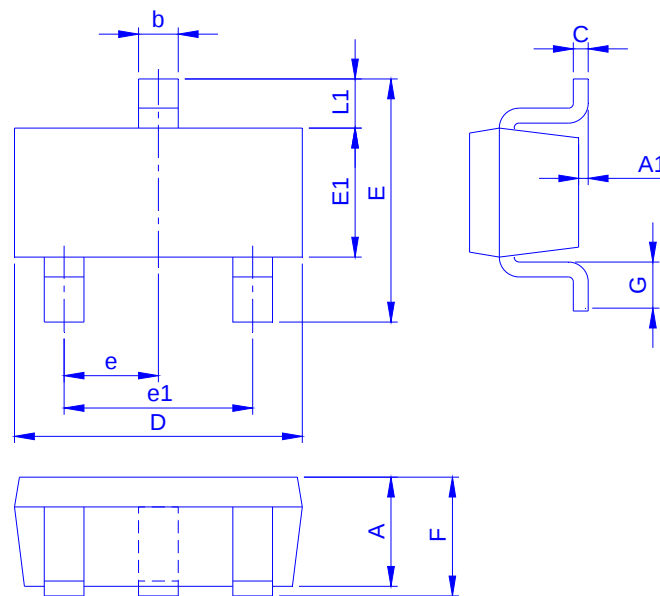


Ordering & Marking Information:

Device Name: EMB32N03JS for SOT-23



Outline Drawing



Dimension in mm

Dimension	A	A1	b	C	D	E	E1	e	e1	F	G	L1
Min.	0.70	0	0.3	0.08	2.80	2.25	1.2	0.90		0.80	0.3	0.50
Typ.					2.90			0.95	1.9			
Max.	1.15	0.1	0.5	0.20	3.02	3.00	1.7	1.00		1.25	0.6	0.75

Footprint

